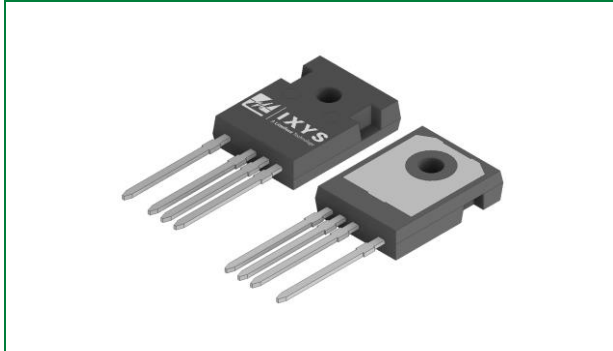


LSIC1MO120G0040 1200 V, 40 mOhm N-Channel SiC MOSFET

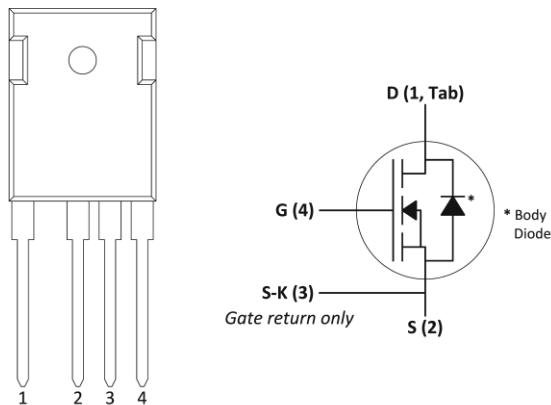


Agency Approvals and Environmental

Environmental Approvals



Pinout Diagram



Product Summary

Characteristic	Value	Unit
V_{DS}	1200	V
Typical $R_{DS(ON)}$	40	mOhm
I_D ($T_C \leq 100^\circ\text{C}$)	50	A

Features

- Optimized for high-frequency, high-efficiency applications
- Extremely low gate charge and output capacitance
- Low gate resistance for high-frequency switching
- Normally-off operations at all temperatures
- Ultra-low on-resistance
- Optimized package with separate driver source pin
- RoHS compliant, lead-free, and halogen-free

Applications

- High-frequency applications
- Solar Inverters
- Switch Mode Power Supplies
- UPS
- Motor Drives
- High Voltage DC/DC Converters
- Battery Chargers
- Induction Heating

1. Maximum Ratings.....3

2. Thermal Characteristics3

3. Electrical Characteristics.....3

 3.1. Static Characteristics ($T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise specified).....3

 3.2. Dynamic Characteristics ($T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)4

4. Reverse Diode Characteristics ($T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)4

5. Performance Curves5

6. Package Dimensions9

7. Part Numbering and Marking.....9

8. Packing Options.....9

9. Packing Specifications10

1. Maximum Ratings

Characteristic	Symbol	Conditions	Value	Unit
Drain-Source Voltage	V_{DS}	$V_{GS} = 0 \text{ V}$	1200	V
Continuous Drain Current	I_D	$V_{GS} = 20 \text{ V}, T_C = 25 \text{ }^\circ\text{C}$	70	A
		$V_{GS} = 20 \text{ V}, T_C = 100 \text{ }^\circ\text{C}$	50	
Pulsed Drain Current ¹	$I_{D(pulse)}$	$T_C = 25 \text{ }^\circ\text{C}$	130	A
Power Dissipation	P_D	$T_C = 25 \text{ }^\circ\text{C}, T_J = 175 \text{ }^\circ\text{C}$	357	W
Gate-Source Voltage	$V_{GS,MAX}$	Absolute maximum values – Steady state	-6 to +22	V
	$V_{GS,OP,TR}^2$	Transient, $t_{transient} < 300 \text{ nsec}$	-10 to +25	
	$V_{GS,OP}^3$	Recommended DC operating values	-5 to +20	
Operating Junction Temperature	T_J	-	-55 to +175	$^\circ\text{C}$
Storage Temperature	T_{STG}	-	-55 to +150	$^\circ\text{C}$
Lead Temperature for Soldering	T_{sld}	-	260	$^\circ\text{C}$
Mounting Torque	M_D	M3 or 6-32 screw	1.0	Nm
			8.8	in-lb

Footnote 1: Pulse width limited by $T_{J,MAX}$

Footnote 2: See Figure 21. V_{GS} Waveform Definition for further information

Footnote 3: MOSFET can operate with $V_{GS(OFF)} = 0 \text{ V}$. $V_{GS(OFF)} = -5 \text{ V}$ provides added noise margin and faster turn-off speed

2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance, junction-to-case	$R_{th,JC,MAX}$	0.42	$^\circ\text{C/W}$
Maximum Thermal Resistance, junction-to-ambient	$R_{th,JA,MAX}$	40	$^\circ\text{C/W}$

3. Electrical Characteristics

3.1. Static Characteristics ($T_J = 25 \text{ }^\circ\text{C}$ unless otherwise specified)

Characteristic	Symbol	Conditions	Value			Unit
			Min	Typ	Max	
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0 \text{ V}, I_D = 100 \text{ } \mu\text{A}$	1200	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 1200 \text{ V}, V_{GS} = 0 \text{ V}$	-	<1	100	μA
		$V_{DS} = 1200 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 175 \text{ }^\circ\text{C}$	-	<1	-	
Gate Leakage Current	$I_{GSS,F}$	$V_{GS} = 22 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	100	nA
	$I_{GSS,R}$	$V_{GS} = -6 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	100	
Drain-Source On-State Resistance	$R_{DS(ON)}$	$I_D = 40 \text{ A}, V_{GS} = 20 \text{ V}$	-	40	50	m Ω
		$I_D = 40 \text{ A}, V_{GS} = 20 \text{ V}, T_J = 175 \text{ }^\circ\text{C}$	-	65	-	
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_D = 20 \text{ mA}$	1.8	2.7	4	V
		$V_{DS} = V_{GS}, I_D = 20 \text{ mA}, T_J = 175 \text{ }^\circ\text{C}$	-	1.7	-	
Gate Resistance	R_G	Resonance method, Drain-Source shorted ¹	-	0.8	-	Ω

Footnote 1: For a description of the resonance method for measuring R_G , refer to the JEDEC Standard JESD24-11 test method

3.2. Dynamic Characteristics (T_J = 25 °C unless otherwise specified)

Characteristic	Symbol	Conditions	Value			Unit
			Min	Typ	Max	
Turn-On Switching Energy	E _{ON}	V _{DD} = 800 V, I _D = 40 A, V _{GS} = -5 / +20 V, R _{G,ext} = 2.5 Ω, L = 350 μH, FWD = LSIC2SD120A20	-	380	-	μJ
Turn-Off Switching Energy	E _{OFF}		-	92	-	
Total Per-Cycle Switching Energy	E _{TS}		-	472	-	
Input Capacitance	C _{ISS}	V _{DD} = 800 V, V _{GS} = 0 V, f = 1 MHz, V _{AC} = 25 mV	-	3170	-	pF
Output Capacitance	C _{OSS}		-	140	-	
Reverse Transfer Capacitance	C _{RSS}		-	13	-	
COSS Stored Energy	E _{OSS}		-	45	-	
Total Gate Charge	Q _g	V _{DD} = 800 V, I _D = 40 A, V _{GS} = -5 / +20 V	-	175	-	nC
Gate-Source Charge	Q _{gs}		-	53	-	
Gate-Drain Charge	Q _{gd}		-	58	-	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 800 V, I _D = 40 A, V _{GS} = -5 / +20 V, R _{G,ext} = 2 Ω, R _L = 20 Ω, Timing relative to V _{DS}	-	13	-	ns
Rise Time	t _r		-	9	-	
Turn-Off Delay Time	t _{d(off)}		-	22	-	
Fall Time	t _f		-	8	-	

4. Reverse Diode Characteristics (T_J = 25 °C unless otherwise specified)

Characteristic	Symbol	Conditions	Value			Unit
			Min	Typ	Max	
Diode Forward Voltage	V _{SD}	I _S = 20 A, V _{GS} = -5 V	-	4.3	-	V
		I _S = 20 A, V _{GS} = -5 V, T _J = 175 °C	-	3.8	-	
Continuous Diode Forward Current	I _S	V _{GS} = -5 V, T _C = 25 °C	-	-	60	A
Peak Diode Forward Current ¹	I _{SP}		-	-	130	
Reverse Recovery Time	t _{rr}	V _{GS} = -5 V, I _S = 40 A, V _R = 800 V, dI/dt = 8.4 A/ns	-	13	-	ns
Reverse Recovery Charge	Q _{rr}		-	403	-	nC
Peak Reverse Recovery Current	I _{rm}		-	51	-	A

Footnote 1: Pulse width limited by T_{J,MAX}

5. Performance Curves

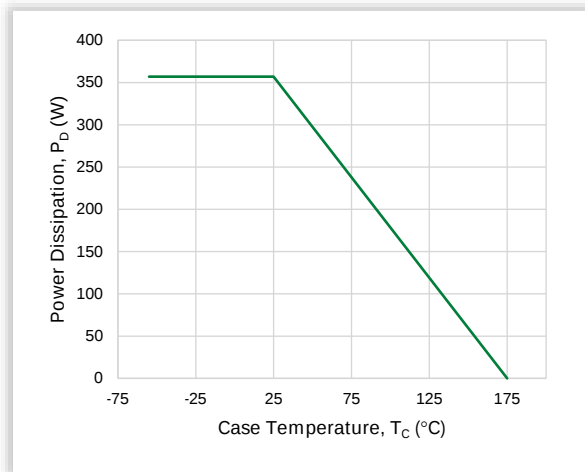
Figure 1. Maximum Power Dissipation ($T_J = 175^\circ\text{C}$)

Figure 2. Typical Transfer Characteristics

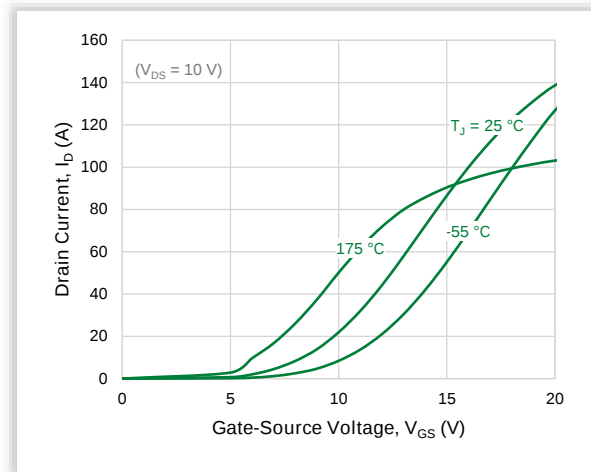
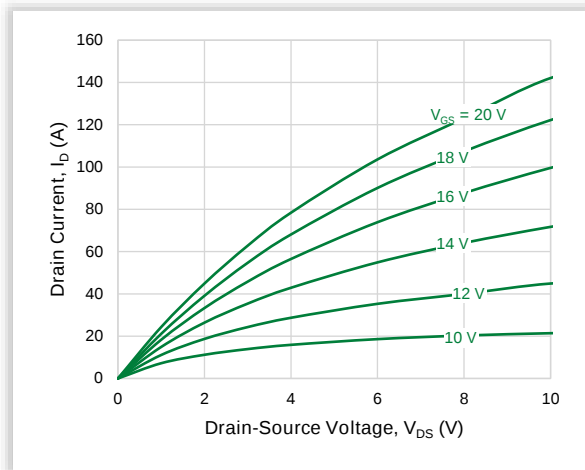
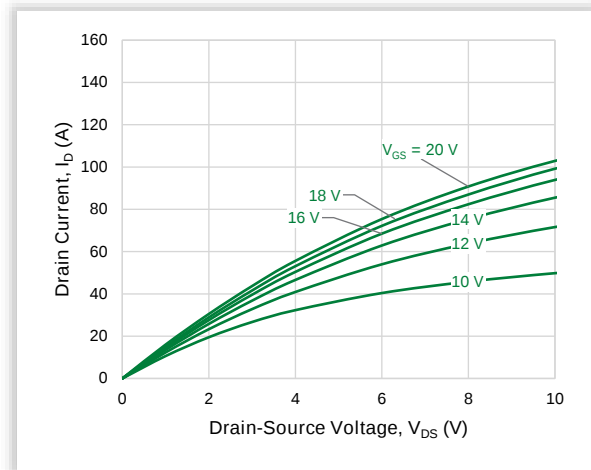
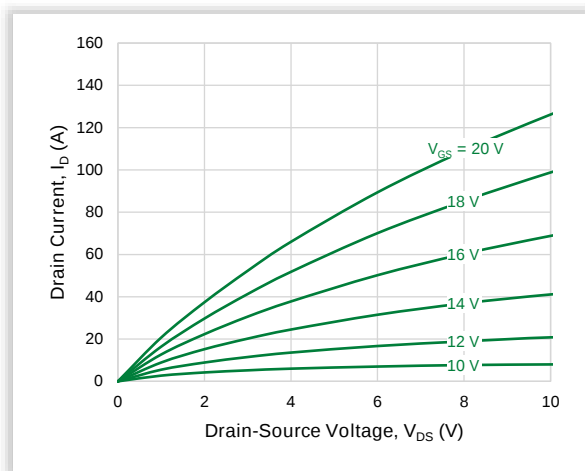
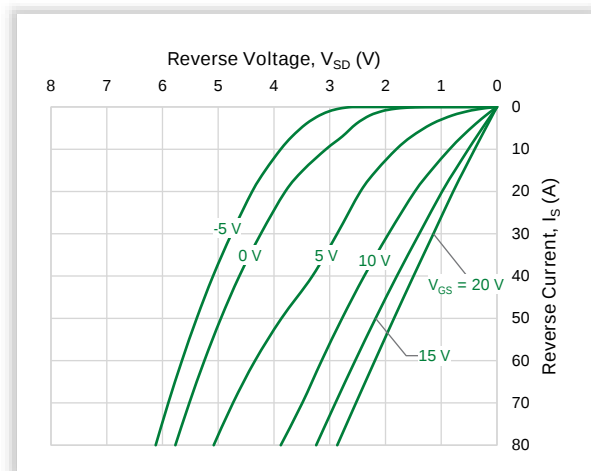
Figure 3. Typical Output Characteristics ($T_J = 25^\circ\text{C}$)Figure 4. Typical Output Characteristics ($T_J = 175^\circ\text{C}$)Figure 5. Typical Output Characteristics ($T_J = -55^\circ\text{C}$)Figure 6. Typical Reverse Conduction Characteristics ($T_J = 25^\circ\text{C}$)

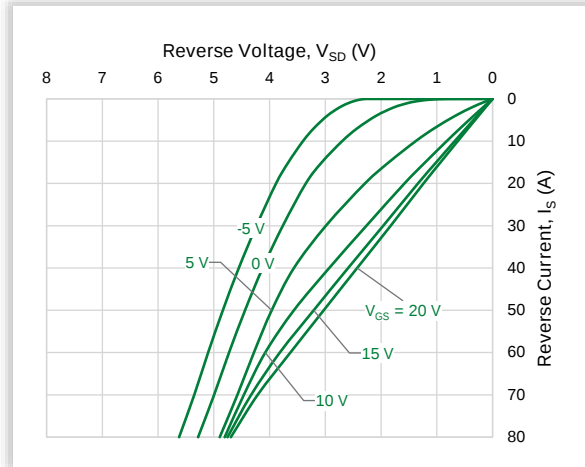
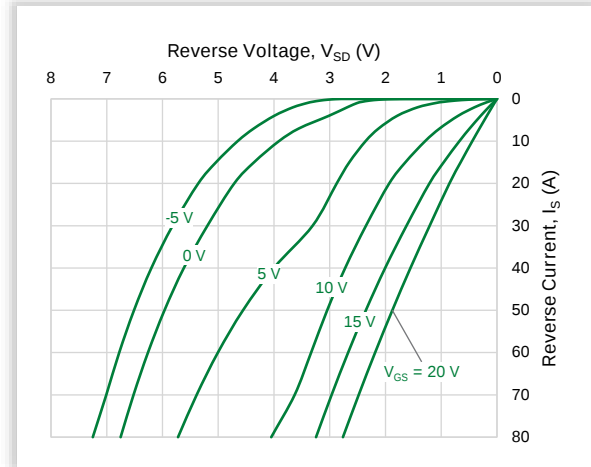
Figure 7. Typical Reverse Conduction Characteristics ($T_J = 175\text{ }^{\circ}\text{C}$)Figure 8. Typical Reverse Conduction Characteristics ($T_J = -55\text{ }^{\circ}\text{C}$)

Figure 9. Transient Thermal Impedance

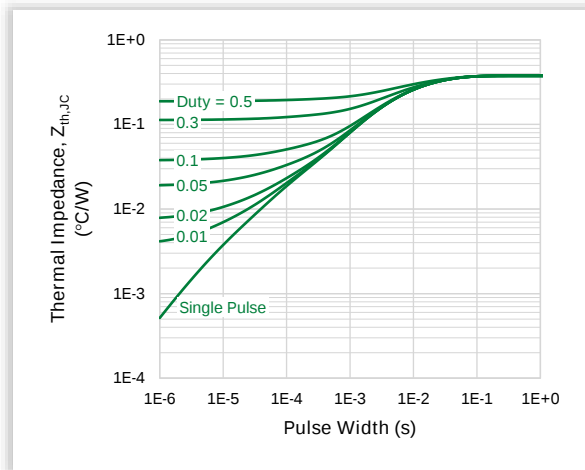
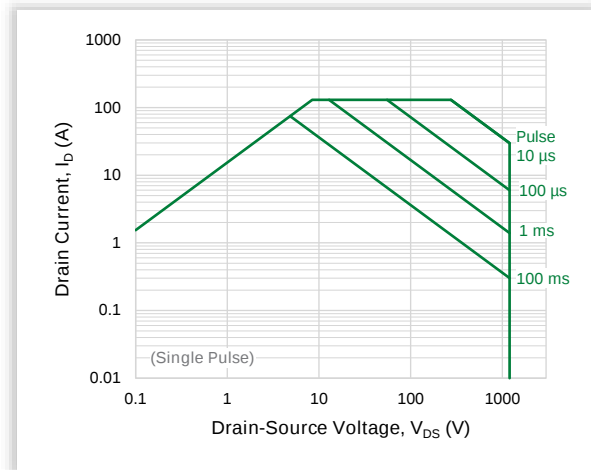
Figure 10. Maximum Safe Operating Area ($T_C = 25\text{ }^{\circ}\text{C}$)

Figure 11. On-resistance vs. Drain Current

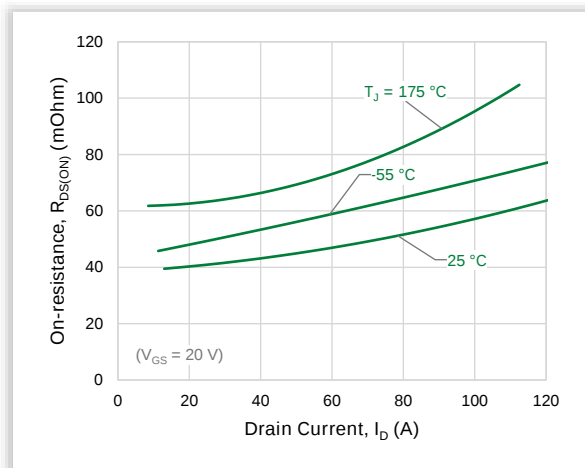


Figure 12. Normalized On-resistance vs. Junction Temperature

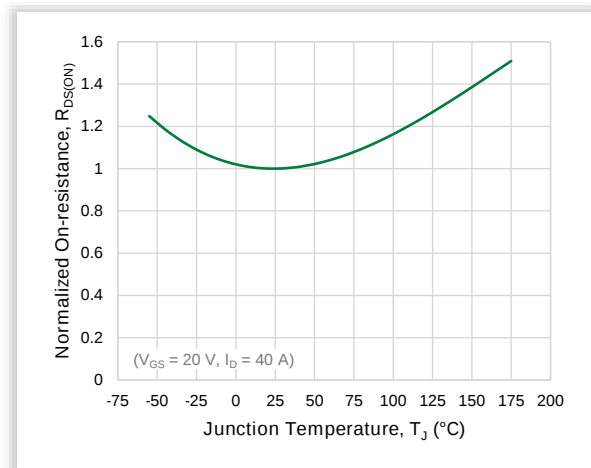


Figure 13. Typical On-resistance vs. Junction Temperature

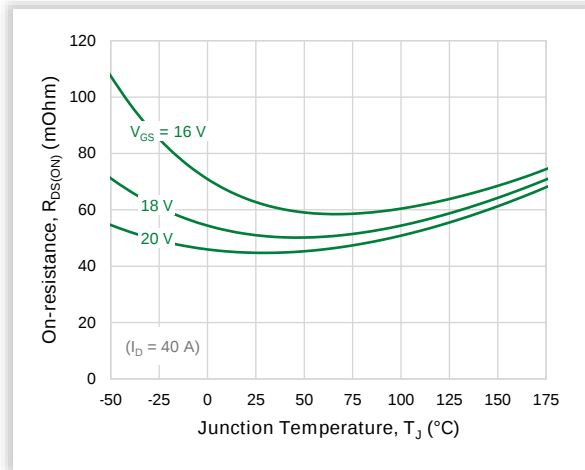


Figure 14. Typical Threshold Voltage

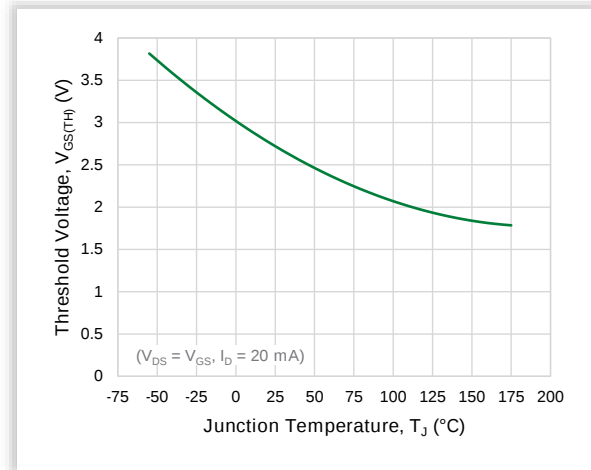


Figure 15. Typical Junction Capacitances up to 1000 V

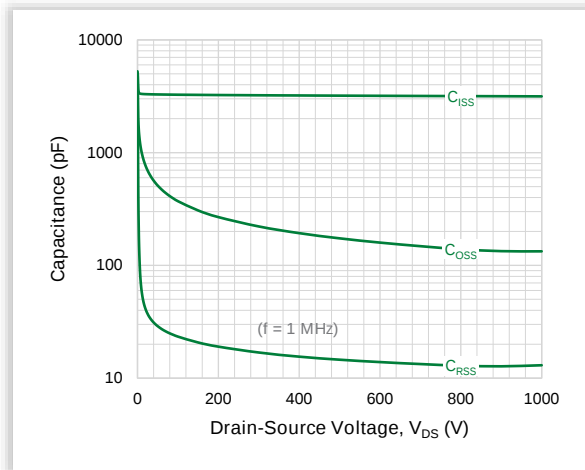


Figure 16. Typical Junction Capacitances up to 200 V

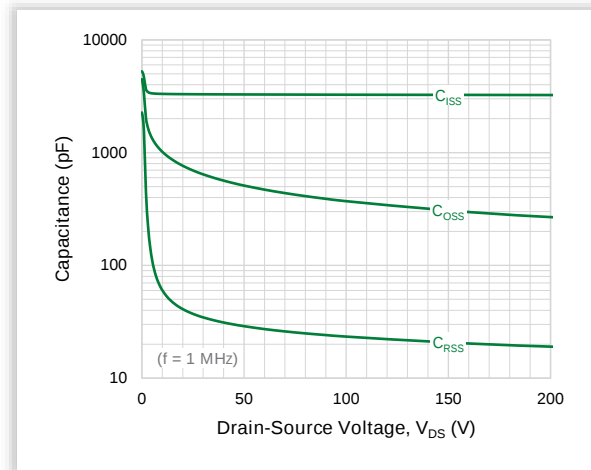


Figure 17. Typical C_oss Stored Energy E_oss

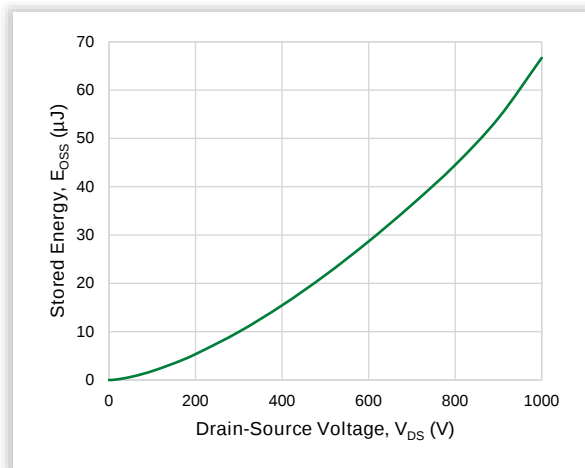


Figure 18. Typical Gate Charge

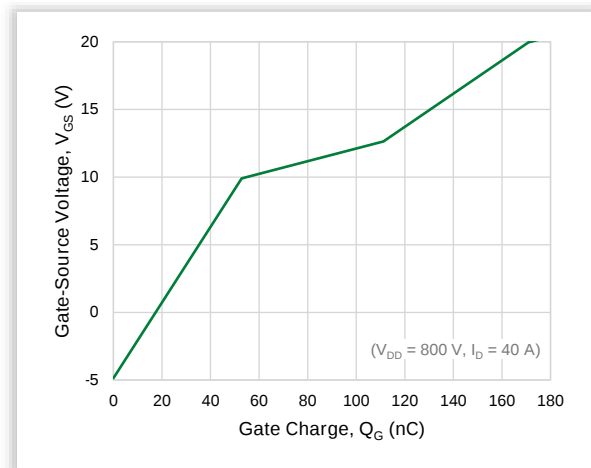


Figure 19. Typical Switching Energy vs. Drain Current

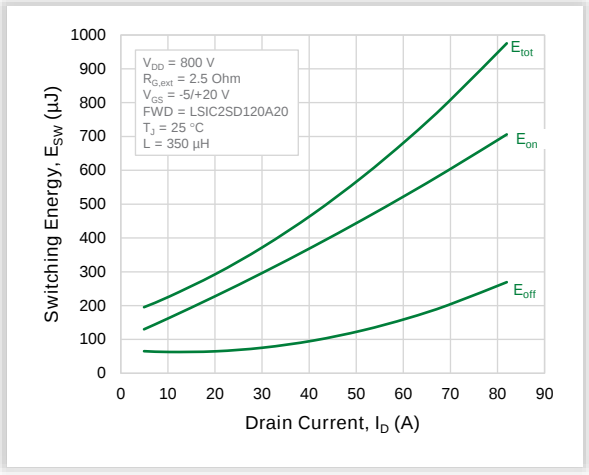


Figure 20. Typical Switching Energy vs. External Gate Resistance

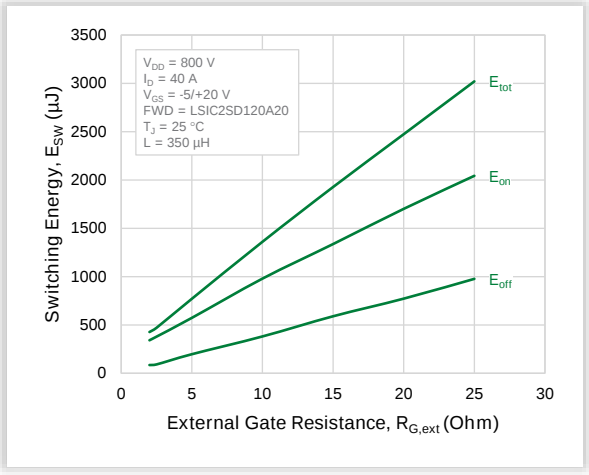
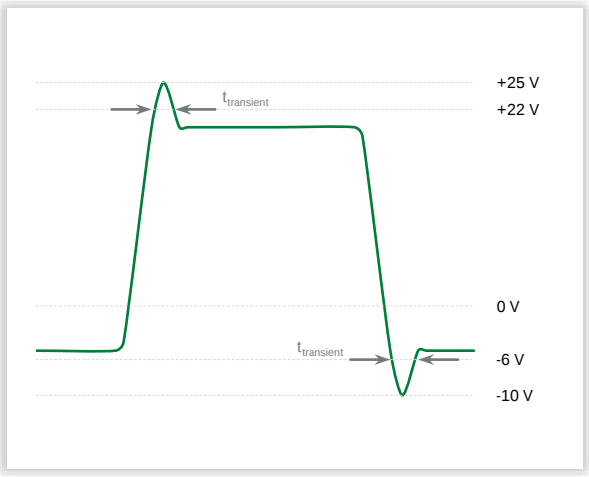
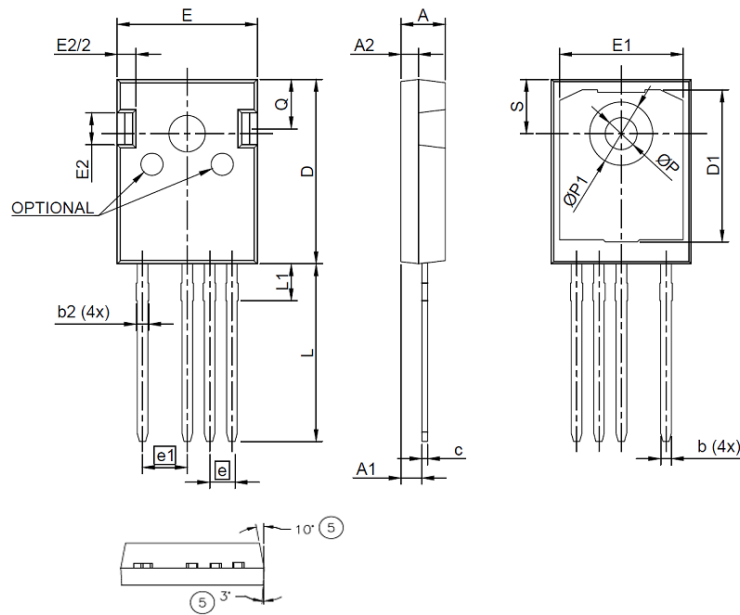


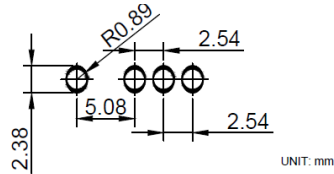
Figure 21. V_{GS} Waveform Definition



6. Package Dimensions



Recommended Hole Pattern Layout:

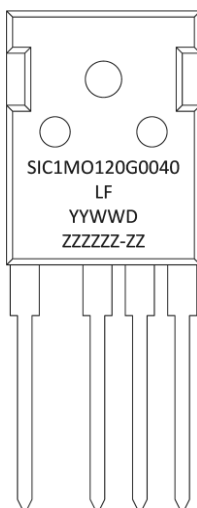


Notes:

1. Dimensioning and tolerancing as per ASME Y14.5 – 2009.
2. Package outline in compliance with JEDEC Standard Var. Ad.
3. Dimension D, E do not include mold flash.
4. Mold draft angles excluded on the table.
5. ϕP to have a maximum draft angle of 1.7° to the top with a maximum hole diameter of 3.912 mm.

Symbol	Millimeters	
	Min	Max
A	4.70	5.31
A1	2.21	2.59
A2	1.50	2.49
b	0.99	1.40
b2	1.65	2.39
c	0.38	0.89
D	20.80	21.46
D1	13.08	-
D2	0.51	1.35
E	15.49	16.26
e	2.54 BSC	
e1	4.83	5.33
E1	13.46	-
E2	3.56	4.06
L	19.81	20.32
L1	-	4.50
ϕP	3.56	3.66
$\phi P1$	7.06	7.39
Q	5.38	6.20
S	6.17 BSC	

7. Part Numbering and Marking

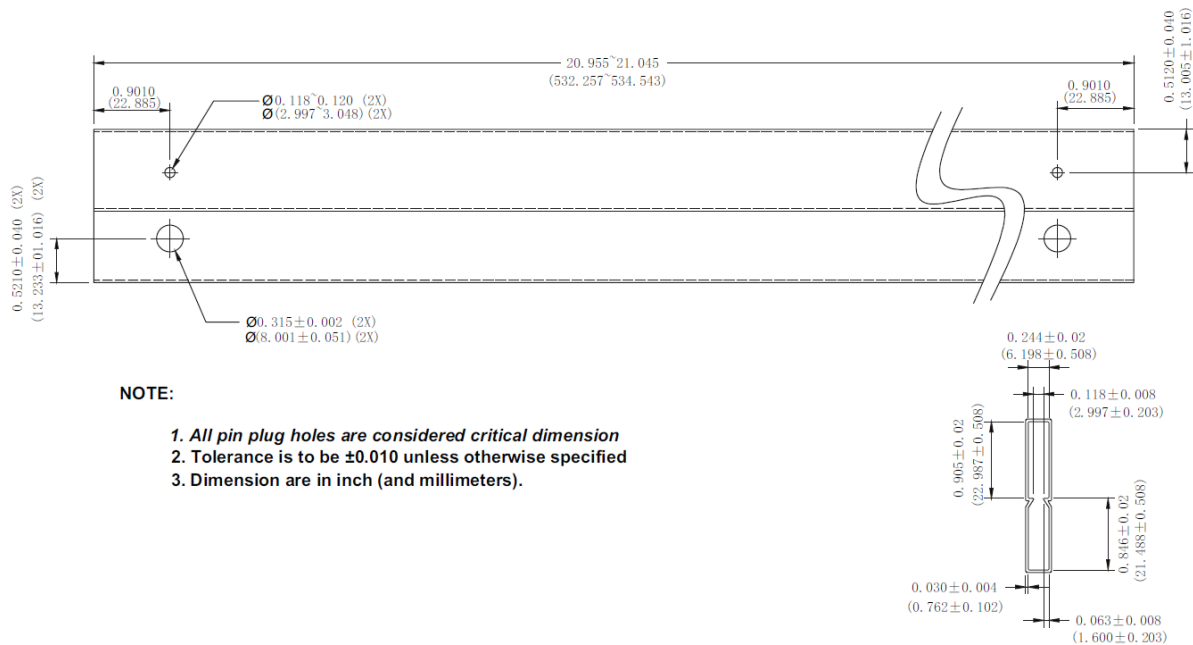


SiC	= SiC
1	= Gen 1
MO	= MOSFET
120	= Voltage Rating (1200 V)
G	= TO-247-4L
0040	= $R_{DS(ON)}$ (40 mOhm)
YY	= Year
WW	= Week
D	= Special Code
ZZZZZZ-ZZ	= Lot Number

8. Packing Options

Part Number	Marking	Packing Mode	M.O.Q.
LSIC1MO120G0040	SIC1MO120G0040	Tube (30 pcs)	450

9. Packing Specifications



For additional information please visit www.Littelfuse.com/powersemi

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